

3 V, LVDS, Quad CMOS Differential Line Receiver

ADN4666

FEATURES

 ± 8 kV ESD IEC 61000-4-2 contact discharge on receiver input pins 400 Mbps (200 MHz) switching rates

100 ps channel-to-channel skew (typical)

100 ps differential skew (typical)

3.3 ns propagation delay (maximum)

3.3 V power supply

High impedance outputs on power-down

Low power design (10 mW quiescent typical)

Interoperable with existing 5 V LVDS drivers

Accepts small swing (350 mV typical) differential

input signal levels

Supports open, short, and terminated input fail-safe

Conforms to TIA/EIA-644 LVDS standard

Industrial operating temperature range of -40°C to $+85^{\circ}\text{C}$

Available in surface-mount SOIC package and low profile TSSOP package

. .

APPLICATIONS

Point-to-point data transmission Multidrop buses Clock distribution networks Backplane receivers

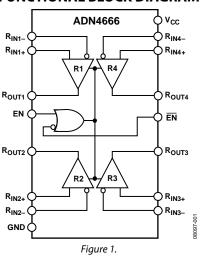
GENERAL DESCRIPTION

The ADN4666 is a quad-channel, CMOS low voltage differential signaling (LVDS) line receiver offering data rates of over 400 Mbps (200 MHz) and ultralow power consumption.

The device accepts low voltage (350 mV typical) differential input signals and converts them to a single-ended, 3 V TTL/CMOS logic level.

The ADN4666 also offers active high and active low enable/disable inputs (EN and $\overline{\rm EN}$) that control all four receivers. These inputs

FUNCTIONAL BLOCK DIAGRAM



disable the receivers and switch the outputs to a high impedance state. Consequently, the outputs of one or more ADN4666 devices can be multiplexed together to reduce the quiescent power consumption to 10 mW typical.

The ADN4666 and its companion driver, the ADN4665, offer a new solution to high speed, point-to-point data transmission and offer a low power alternative to emitter-coupled logic (ECL) or positive emitter-coupled logic (PECL).

TABLE OF CONTENTS

Features	1
Applications	1
Functional Block Diagram	1
General Description	
Revision History	
Specifications	
Timing Specifications	
Absolute Maximum Ratings	

ESD Caution	
Pin Configuration and Function Descriptions	
Typical Performance Characteristics	
Theory of Operation	
Enable Inputs	
Applications Information	
Outline Dimensions	1
Ordering Guide	1.

REVISION HISTORY

6/09—Revision 0: Initial Version

SPECIFICATIONS

 $V_{CC} = 3.0 \text{ V}$ to 3.6 V, $C_L = 15 \text{ pF}$ to GND, all specifications T_{MIN} to T_{MAX} , unless otherwise noted.^{1, 2}

Table 1.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
LVDS INPUTS (R _{INx+} , R _{INx-})						
Differential Input High Threshold at $R_{\text{INx+}},R_{\text{INx-}}{}^3$	V_{TH}		20	100	mV	V _{CM} = 1.2 V, 0.05 V, 2.95 V
Differential Input Low Threshold at R _{INx+} , R _{INx-} ³	V _{TL}	-100	-20		mV	V _{CM} = 1.2 V, 0.05 V, 2.95 V
Common-Mode Voltage Range at R _{INx+} , R _{INx-} ⁴	V_{CMR}	0.1		2.3	V	$V_{ID} = 200 \text{ mV p-p}$
Input Current at R _{INx+} , R _{INx-}	I _{IN}	-10	±5	+10	μΑ	$V_{IN} = 2.8 \text{ V}, V_{CC} = 3.6 \text{ V or } 0 \text{ V}$
		-10	±1	+10	μΑ	$V_{IN} = 0 \text{ V}, V_{CC} = 3.6 \text{ V or } 0 \text{ V}$
		-20	±1	+20	μΑ	$V_{IN} = 3.6 \text{ V}, V_{CC} = 0 \text{ V}$
Input High Voltage	V _{IH}	2.0		V_{CC}	V	
Input Low Voltage	VIL	GND		0.8	V	
Input Current	I _{IN}	-10	±1	+10	μΑ	$V_{IN} = 0 \text{ V or } V_{CC}$, other input = V_{CC} or GND
Input Clamp Voltage	V _{CL}	-1.5	-0.8		V	$I_{CL} = -18 \text{ mA}$
OUTPUTS (R _{OUTx})						
Output High Voltage	V _{OH}	2.7	3.0		V	$I_{OH} = -0.4 \text{ mA}, V_{ID} = 200 \text{ mV}$
		2.7	3.0		V	$I_{OH} = -0.4$ mA, input terminated
		2.7	3.0		V	$I_{OH} = -0.4$ mA, input shorted
Output Low Voltage	V _{OL}		0.1	0.25	V	$I_{OL} = 2 \text{ mA}, V_{ID} = -200 \text{ mV}$
Output Short-Circuit Current ⁵	los	-15	-48	-120	mA	Outputs enabled, V _{OUT} = 0 V
Output Off State Current	l _{oz}	-10	±1	+10	μΑ	Outputs disabled, $V_{OUT} = 0 \text{ V or } V_{CC}$
POWER SUPPLY						
No Load Supply, Current Receivers Enabled	lcc		10	15	mA	EN and $\overline{EN} = V_{CC}$ or GND, inputs open
No Load Supply, Current Receivers Disabled	Iccz		3	5	mA	$EN = GND$ and $\overline{EN} = V_{CC}$, inputs open
ESD PROTECTION						
R _{INx+} , R _{INx-} Pins			±8		kV	IEC 61000-4-2 contact discharge
			±15		kV	Human body model
All Pins Except R _{INx+} , R _{INx-}			±4		kV	Human body model

¹ Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground, unless otherwise specified.

 $^{^2}$ All typical values are given for $V_{CC} = 3.3 \text{ V}$ and $T_A = 25^{\circ}\text{C}$.

 $^{^3}$ V_{CC} is always higher than the R_{INX+} and R_{INX+} and R_{INX+} and R_{INX+} and R_{INX+} and R_{INX+} have a voltage range of -0.2 V to V_{CC} - V_{ID}/2. However, to be compliant with ac specifications, the common-mode voltage range is 0.1 V to 2.3 V.

 $^{^4}$ V_{CMR} is reduced for larger input differential voltage (V_{ID}). For example, if V_{ID} is 400 mV, V_{CMR} is 0.2 V to 2.2 V. The fail-safe condition with inputs shorted is not supported over the common-mode range of 0 V to 2.4 V, but is supported only with inputs shorted and no external common-mode voltage applied. V_{ID} up to V_{CC} – 0 V can be applied to the R_{INX+}/R_{INX-} inputs with the common-mode voltage set to V_{CC}/2. Propagation delay and differential pulse skew decrease when V_{ID} is increased from 200 mV to 400 mV. Skew specifications apply for 200 mV \leq V_{ID} \leq 800 mV over the common-mode range.

⁵ Output short-circuit current (los) is specified as magnitude only; a minus sign indicates direction only. Note that only one output should be shorted at a time; do not exceed the maximum junction temperature specification (150°C).

TIMING SPECIFICATIONS

 $V_{CC} = 3.0 \text{ V}$ to 3.6 V, $C_L = 15 \text{ pF}$ to GND, all specifications T_{MIN} to T_{MAX} , unless otherwise noted.

Table 2.

Parameter ²	Symbol	Min	Typ ³	Max	Unit	Test Conditions/Comments ^{4, 5}
AC CHARACTERISTICS						
Differential Propagation Delay, High to Low	t _{PHLD}	1.8		3.3	ns	$C_L = 15 \text{ pF, } V_{ID} = 300 \text{ mV} \text{ (see Figure 2 and Figure 3)}$
Differential Propagation Delay, Low to High	t _{PLHD}	1.8		3.3	ns	$C_L = 15 \text{ pF, } V_{ID} = 300 \text{ mV (see Figure 2 and Figure 3)}$
Differential Pulse Skew ⁶ t _{PHLD} - t _{PLHD}	t _{SKD1}	0	0.1	0.35	ns	$C_L = 15 \text{ pF, } V_{ID} = 300 \text{ mV} \text{ (see Figure 2 and Figure 3)}$
Differential Channel-to-Channel Skew (Same Device) ⁷	t _{SKD2}	0	0.1	0.5	ns	$C_L = 15 \text{ pF}$, $V_{ID} = 300 \text{ mV}$ (see Figure 2 and Figure 3)
Differential Part-to-Part Skew ⁸	t _{SKD3}			1.0	ns	$C_L = 15 \text{ pF, } V_{ID} = 300 \text{ mV (see Figure 2 and Figure 3)}$
Differential Part-to-Part Skew ⁹	t _{SKD4}			1.5	ns	$C_L = 15 \text{ pF, } V_{ID} = 300 \text{ mV (see Figure 2 and Figure 3)}$
Rise Time	t _{TLH}		0.35	1.2	ns	$C_L = 15 \text{ pF, } V_{ID} = 300 \text{ mV (see Figure 2 and Figure 3)}$
Fall Time	t _{THL}		0.35	1.2	ns	$C_L = 15 \text{ pF, } V_{ID} = 300 \text{ mV (see Figure 2 and Figure 3)}$
Disable Time, High to Z	t _{PHZ}		8	12	ns	$R_L = 2 \text{ k}\Omega$, $C_L = 15 \text{ pF}$ (see Figure 4 and Figure 5)
Disable Time, Low to Z	t _{PLZ}		8	12	ns	$R_L = 2 \text{ k}\Omega$, $C_L = 15 \text{ pF}$ (see Figure 4 and Figure 5)
Enable Time, Z to High	t _{PZH}		11	17	ns	$R_L = 2 \text{ k}\Omega$, $C_L = 15 \text{ pF}$ (see Figure 4 and Figure 5)
Enable Time, Z to Low	t _{PZL}		11	17	ns	$R_L = 2 \text{ k}\Omega$, $C_L = 15 \text{ pF}$ (see Figure 4 and Figure 5)
Maximum Operating Frequency 10	f _{MAX}	200	250		MHz	All channels switching

 $^{^{1}}$ Generator waveform for all tests, unless otherwise specified: f = 1 MHz, $Z_{O} = 50 \Omega$, t_{TLH} and t_{THL} (0% to 100%) ≤ 3 ns for R_{INX-r}/R_{INX-r}

Test Circuits and Timing Diagrams

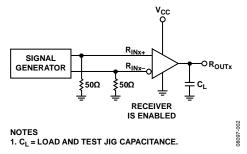


Figure 2. Test Circuit for Receiver Propagation Delay and Transition Time

² AC parameters are guaranteed by design and characterization.

³ All typical values are given for $V_{CC} = 3.3 \text{ V}$ and $T_A = 25^{\circ}\text{C}$.

⁴ Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground, unless otherwise specified.

⁵ C_L includes load and jig capacitance.

⁶ t_{SKD1} is the magnitude difference in the differential propagation delay time between the positive-going edge and the negative-going edge of the same channel.

⁷ Channel-to-channel skew, t_{SKD2}, is defined as the difference between the propagation delay of one channel and that of the others on the same chip with any event on the inputs.

⁸ t_{SKD3} part-to-part skew is the differential channel-to-channel skew of any event between devices. The t_{SKD3} specification applies to devices at the same V_{CC} and within 5°C of each other within the operating temperature range.

⁹ t_{SKD4} part-to-part skew is the differential channel-to-channel skew of any event between devices. The t_{SKD4} specification applies to devices over the recommended operating temperature and voltage ranges and across process distribution. t_{SKD4} is defined as |maximum – minimum| differential propagation delay.

 $^{^{10}}$ f_{MAX} generator input conditions: \hat{f} = 200 MHz, t_{TLH} = t_{THL} < 1 ns (0% to 100%), 50% duty cycle, differential (1.05 V to 1.35 V p-p). f_{MAX} generator output criteria: 60%/40% duty cycle, V_{OL} (maximum = 0.4 V), V_{OH} (minimum = 2.7 V), and load = 15 pF (stray plus probes).

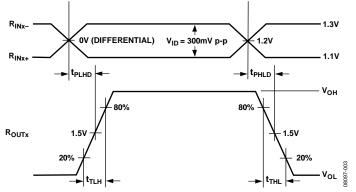
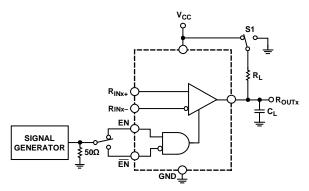


Figure 3. Receiver Propagation Delay and Transition Time Waveforms



NOTES

- C_L INCLUDES LOAD AND TEST JIG CAPACITANCE.
 S1 CONNECTED TO V_{CC} FOR t_{PZL} AND t_{PLZ} MEASUREMENTS.
- 3. S1 CONNECTED TO GND FOR $t_{\mbox{\scriptsize PZH}}$ AND $t_{\mbox{\scriptsize PHZ}}$ MEASUREMENTS.

Figure 4. Test Circuit for Receiver Enable/Disable Delay

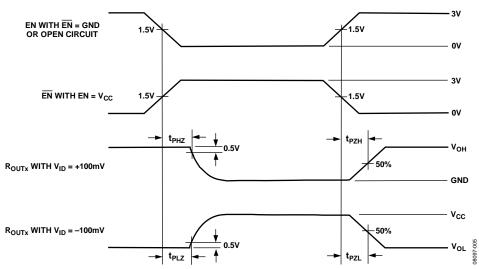


Figure 5. Receiver Enable/Disable Delay Waveforms

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise noted.

Table 3.

Parameter	Rating
V _{CC} to GND	−0.3 V to +4 V
Input Voltage (R _{INx+} , R _{INx-}) to GND	$-0.3 \text{ V to V}_{CC} + 0.3 \text{ V}$
Enable Input Voltage (EN, EN) to GND	$-0.3 \text{ V to V}_{CC} + 0.3 \text{ V}$
Output Voltage (Routx) to GND	$-0.3 \text{ V to V}_{CC} + 0.3 \text{ V}$
Industrial Operating Temperature Range	−40°C to +85°C
Storage Temperature Range	−65°C to +150°C
Maximum Junction Temperature (TJMAX)	150°C
θ_{JA} Thermal Impedance	150.4°C/W
Power Dissipation	$(T_{JMAX} - T_{A})/\theta_{JA}$
Reflow Soldering Peak Temperature, Pb-Free	260°C ± 5°C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

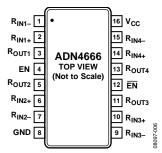


Figure 6. Pin Configuration

Table 4. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	R _{IN1} _	Receiver Channel 1 Inverting Input. When this input is more negative than R _{IN1+} , R _{OUT1} is high. When this input is more positive than R _{IN1+} , R _{OUT1} is low.
2	R _{IN1+}	Receiver Channel 1 Noninverting Input. When this input is more positive than R_{IN1-} , R_{OUT1} is high. When this input is more negative than R_{IN1-} , R_{OUT1} is low.
3	R _{OUT1}	Receiver Channel 1 Output (3 V TTL/CMOS). If the differential input voltage between $R_{\text{IN1-}}$ and $R_{\text{IN1-}}$ is positive, this output is high. If the differential input voltage is negative, this output is low.
4	EN	Active High Enable and Power-Down Input (3 V TTL/CMOS). When EN is low and \overline{EN} is high, the receiver outputs are disabled and are in a high impedance state. When EN is high and \overline{EN} is low or when EN is low and \overline{EN} is low, the receiver outputs are enabled. When EN is high and \overline{EN} is high, the receiver outputs are enabled.
5	R _{ОUТ2}	Receiver Channel 2 Output (3 V TTL/CMOS). If the differential input voltage between R _{IN2+} and R _{IN2-} is positive, this output is high. If the differential input voltage is negative, this output is low.
6	R _{IN2+}	Receiver Channel 2 Noninverting Input. When this input is more positive than R _{IN2-} , R _{OUT2} is high. When this input is more negative than R _{IN2-} , R _{OUT2} is low.
7	R _{IN2} -	Receiver Channel 2 Inverting Input. When this input is more negative than R_{IN2+} , R_{OUT2} is high. When this input is more positive than R_{IN2+} , R_{OUT2} is low.
8	GND	Ground Reference Point for All Circuitry on the Part.
9	R _{IN3} -	Receiver Channel 3 Inverting Input. When this input is more negative than R_{IN3+} , R_{OUT3} is high. When this input is more positive than R_{IN3+} , R_{OUT3} is low.
10	R _{IN3+}	Receiver Channel 3 Noninverting Input. When this input is more positive than R _{IN3} -, R _{OUT3} is high. When this input is more negative than R _{IN3} -, R _{OUT3} is low.
11	R _{OUT3}	Receiver Channel 3 Output (3 VTTL/CMOS). If the differential input voltage between R _{IN3+} and R _{IN3-} is positive, this output is high. If the differential input voltage is negative, this output is low.
12	ĒN	Active Low Enable and Power-Down Input with Pull-Down (3 V TTL/CMOS).). When EN is low and \overline{EN} is high, the receiver outputs are disabled and are in a high impedance state. When EN is high and \overline{EN} is low or when EN is low and \overline{EN} is low, the receiver outputs are enabled. When EN is high and \overline{EN} is high, the receiver outputs are enabled.
13	R _{OUT4}	Receiver Channel 4 Output (3 VTTL/CMOS). If the differential input voltage between R _{IN4+} and R _{IN4-} is positive, this output is high. If the differential input voltage is negative, this output is low.
14	R _{IN4+}	Receiver Channel 4 Noninverting Input. When this input is more positive than R _{IN4} -, R _{OUT4} is high. When this input is more negative than R _{IN4} -, R _{OUT4} is low.
15	R _{IN4}	Receiver Channel 4 Inverting Input. When this input is more negative than R _{IN4+} , R _{OUT4} is high. When this input is more positive than R _{IN4+} , R _{OUT4} is low.
16	V _{CC}	Power Supply Input. The ADN4666 can be operated from 3.0 V to 3.6 V.

TYPICAL PERFORMANCE CHARACTERISTICS

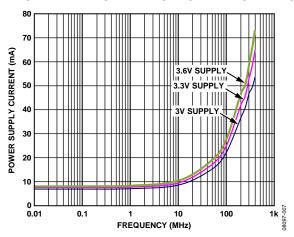


Figure 7. Power Supply Current vs. Frequency

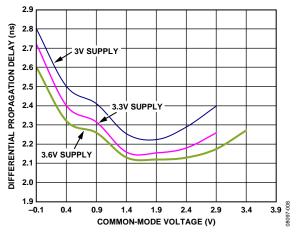


Figure 8. Differential Propagation Delay (tplhD) vs. Common-Mode Voltage, 25℃

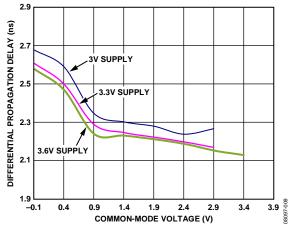


Figure 9. Differential Propagation Delay (tphld) vs. Common-Mode Voltage, 25°C

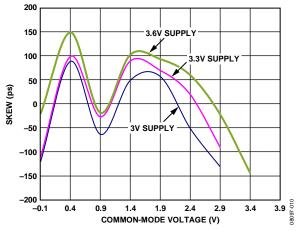


Figure 10. Skew vs. Common-Mode Voltage, 25℃

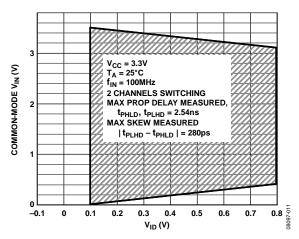


Figure 11. Typical Common-Mode Range Variation with Respect to the Amplitude of the Differential Input

THEORY OF OPERATION

The ADN4666 is a quad-channel line receiver for low voltage differential signaling (LVDS). It takes a differential input signal of 350 mV typical and converts it into a single-ended, 3 V TTL/CMOS logic signal.

A differential current input signal, received via a transmission medium such as a twisted pair cable, develops a voltage across a termination resistor, $R_{\rm T}.$ This resistor is chosen to match the characteristic impedance of the medium, typically around 100 $\Omega.$ The differential voltage is detected by the receiver and converted back into a single-ended logic signal.

When the noninverting receiver input, $R_{\rm INx+}$, is positive with respect to the inverting input, $R_{\rm INx-}$ (that is, when current flows through $R_{\rm T}$ from $R_{\rm INx+}$ to $R_{\rm INx-}$), $R_{\rm OUTx}$ is high. When the noninverting receiver input, $R_{\rm INx+}$, is negative with respect to the inverting input, $R_{\rm INx-}$ (that is, when current flows through $R_{\rm T}$ from $R_{\rm INx-}$ to $R_{\rm INx+}$), $R_{\rm OUTx}$ is low.

Using the ADN4665 as a driver, the received differential current is between ± 2.5 mA and ± 4.5 mA (± 3.5 mA typical), developing between ± 250 mV and ± 450 mV across a 100 Ω termination resistor. The received voltage is centered around the receiver offset of 1.2 V. Therefore, the noninverting receiver input is typically 1.375 V (that is, 1.2 V + [350 mV/2]) and the inverting receiver input is 1.025 V (that is, 1.2 V – [350 mV/2]) for a Logic 1. For a Logic 0, the inverting and noninverting input voltages are reversed. Note that because the differential voltage reverses polarity, the peak-to-peak voltage swing across R_T is twice the differential voltage.

Current-mode drivers offer considerable advantages over voltage-mode drivers, such as the RS-422 drivers. The operating current remains fairly constant with increased switching frequency, whereas the operating current of voltage-mode drivers increases exponentially in most cases. This increase is caused by the overlap as internal gates switch between high and low, causing currents to flow from $V_{\rm CC}$ to ground. A current-mode device reverses a constant current between its two outputs, with no significant overlap currents.

This is similar to emitter-coupled logic (ECL) and positive emitter-coupled logic (PECL), but without the high quiescent current of ECL and PECL.

ENABLE INPUTS

The ADN4666 has active high and active low enable inputs that put all the logic outputs into a high impedance state when disabled, reducing device current consumption from 10 mA typical to 3 mA typical. See Table 5 for a truth table of the enable inputs.

Table 5. Enable Inputs Truth Table

Pin I	Logic Level				
EN	EN	R _{INx+}	R _{INx-}	R _{OUTx}	
Low	High	X ¹	X ¹	High-Z	
Low	Low	1.025 V	1.375 V	0	
Low	Low	1.375 V	1.025 V	1	
High	Low	1.025 V	1.375 V	0	
High	Low	1.375 V	1.025 V	1	

¹ X = don't care.

APPLICATIONS INFORMATION

Figure 12 shows a typical application for point-to-point data transmission using the ADN4665 as the driver and the ADN4666 as the receiver.

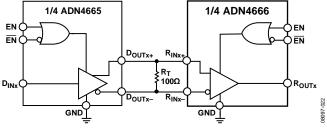
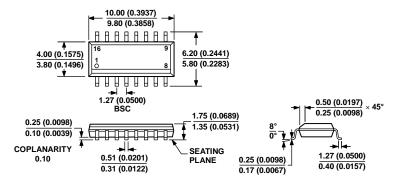


Figure 12. Typical Application Circuit

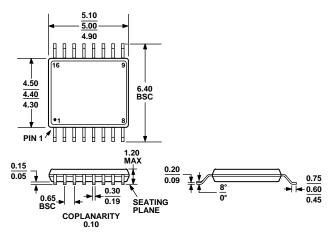
OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-012-AC

CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 13. 16-Lead Standard Small Outline Package [SOIC_N] Narrow Body (R-16) Dimensions shown in millimeters and (inches)



COMPLIANT TO JEDEC STANDARDS MO-153-AB

Figure 14. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16) Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADN4666ARZ ¹	−40°C to +85°C	16-Lead Thin Standard Small Outline Package [SOIC_N]	R-16
ADN4666ARZ-REEL7 ¹	-40°C to +85°C	16-Lead Thin Standard Small Outline Package [SOIC_N]	R-16
ADN4666ARUZ ¹	-40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADN4666ARUZ-REEL7 ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16

¹ Z = RoHS Compliant Part.

NOTES

ADN4666

NOTES